

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	65	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Collector Current - Continuous	I <sub>C</sub>	100	mA
Peak Collector Current	I <sub>CM</sub>	200	mA
Peak Emitter Current	I <sub>EM</sub>	200	mA

## Thermal Characteristics

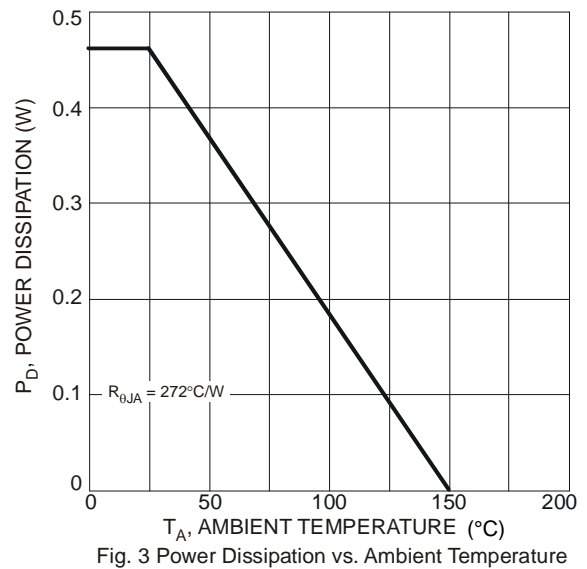
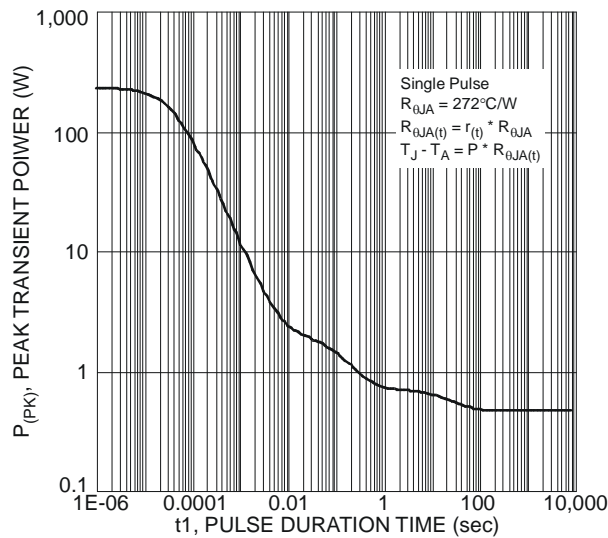
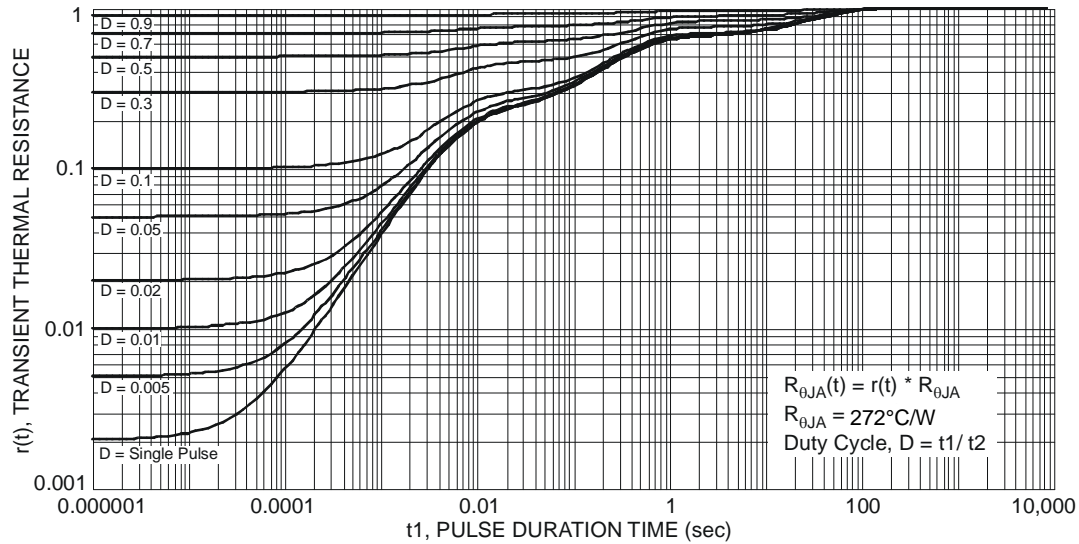
Characteristic	Symbol	Value	Unit
Power Dissipation	P <sub>D</sub>	0.46	W
		1	
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	272	°C/W
		120	
Thermal Resistance, Junction to Leads	R <sub>θJL</sub>	110	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	B

- Notes:
5. For a device surface mounted on minimum recommended pad layout FR-4 PCB with single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The entire exposed collector pad is attached to the heatsink.
  6. Same as Note 5, except device is surface mounted on 25mm X 25mm collector pad heatsink with 1oz copper.
  7. Thermal resistance from junction to solder-point (at the end of the collector lead).
  8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

## Thermal Characteristics

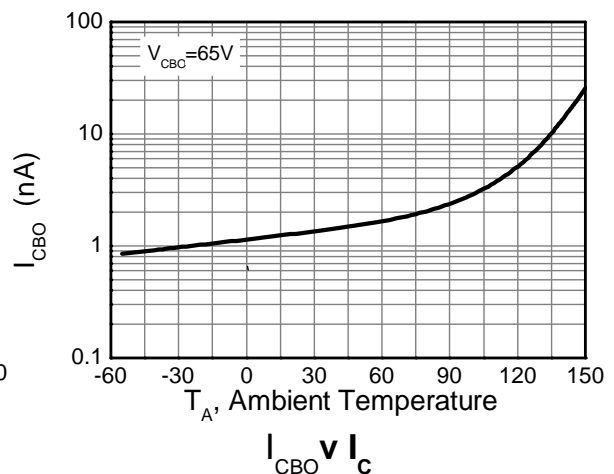
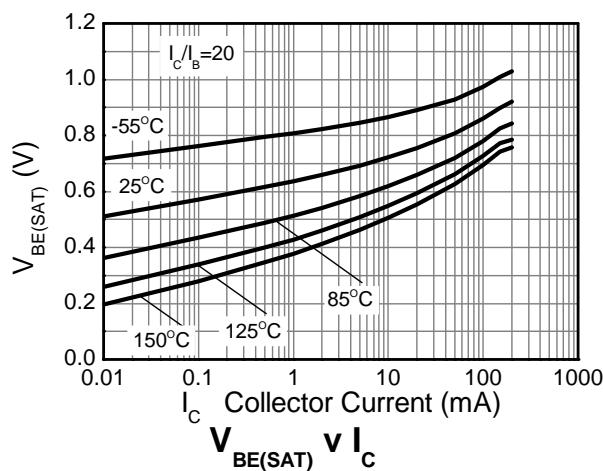
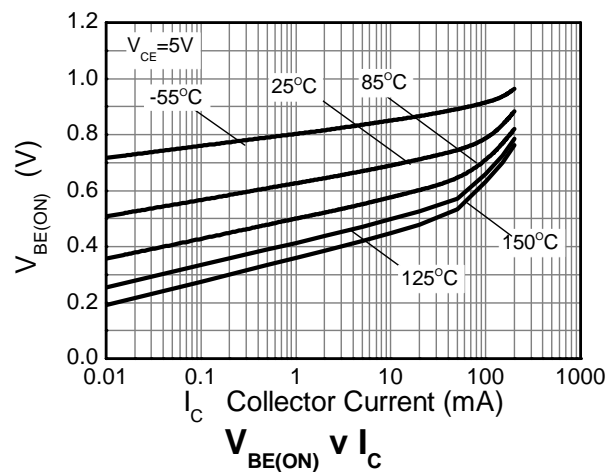
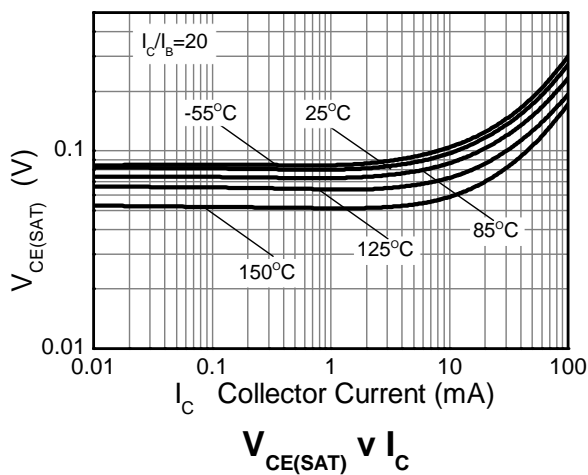
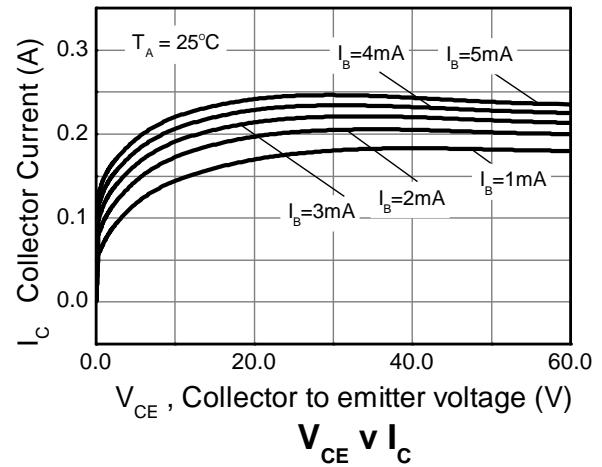
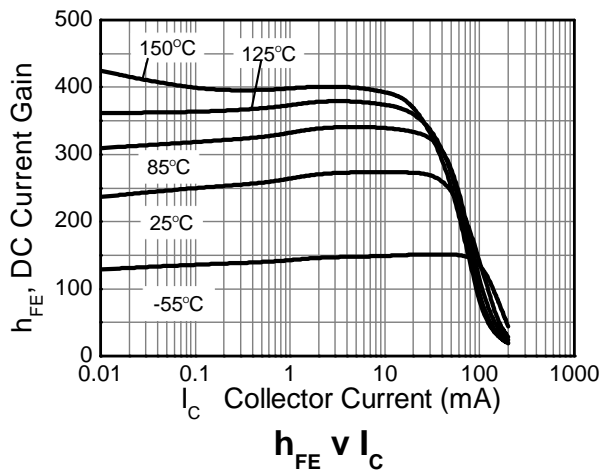


**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

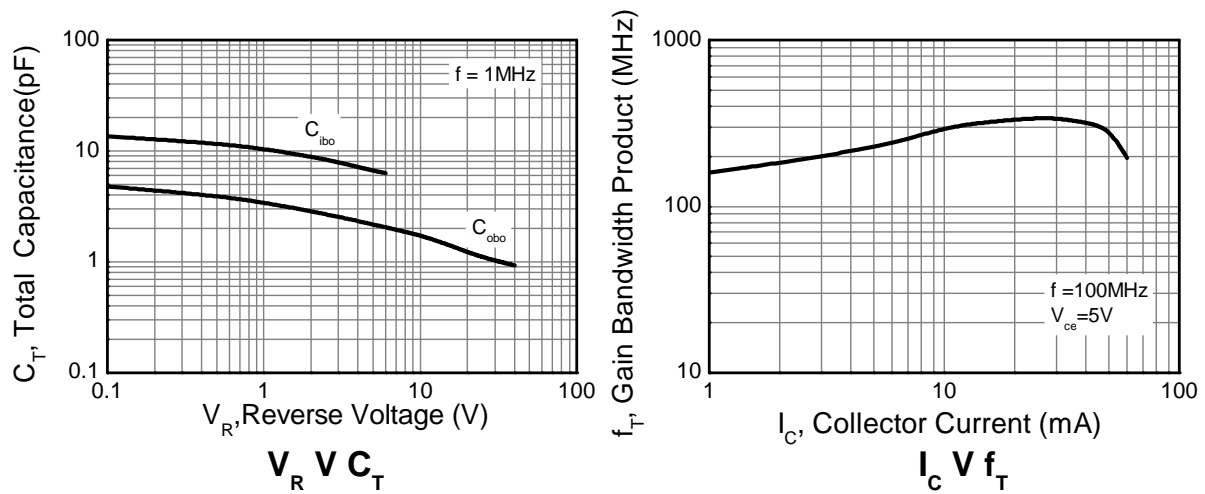
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	80	—	—	V	I <sub>C</sub> = 100μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	65	—	—	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6	—	—	V	I <sub>E</sub> = 100μA, I <sub>C</sub> = 0
Collector Cutoff Current	I <sub>CES</sub>	—	—	15	nA	V <sub>CE</sub> = 65V
Collector Cutoff Current	I <sub>CBO</sub>	—	—	15 5.0	nA μA	V <sub>CB</sub> = 40V V <sub>CB</sub> = 30V, T <sub>A</sub> = +150°C
<b>ON CHARACTERISTICS (Note 9)</b>						
DC Current Gain	h <sub>FE</sub>	200	270	450	—	V <sub>CE</sub> = 5V, I <sub>C</sub> = 2.0mA
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	—	90 220	250 600	mV	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0.5mA I <sub>C</sub> = 100mA, I <sub>B</sub> = 5.0mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	—	720 870	900 —	mV	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0.5mA I <sub>C</sub> = 100mA, I <sub>B</sub> = 5.0mA
Base-Emitter Voltage	V <sub>BE(ON)</sub>	580 —	650 —	700 770	mV	V <sub>CE</sub> = 5V, I <sub>C</sub> = 2.0mA V <sub>CE</sub> = 5V, I <sub>C</sub> = 10mA
<b>SMALL SIGNAL CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>ibo</sub>	—	6.7	—	pF	V <sub>CB</sub> = 5V, f = 1.0MHz
Output Capacitance	C <sub>obo</sub>	—	1.76	—	pF	V <sub>CB</sub> = 10V, f = 1.0MHz
Current Gain-Bandwidth Product	f <sub>T</sub>	100	300	—	MHz	V <sub>CE</sub> = 5V, I <sub>C</sub> = 10mA, f = 100MHz
Noise Figure	NF	—	2	10	dB	V <sub>CE</sub> = 5V, I <sub>C</sub> = 200μA, R <sub>S</sub> = 2.0kΩ, f = 1.0kHz, Δf = 200Hz
Delay Time	t <sub>D</sub>	—	11.2	—	ns	V <sub>CC</sub> = 30V, I <sub>C</sub> = 150mA, I <sub>B1</sub> = -I <sub>B2</sub> = 15mA
Rise Time	t <sub>R</sub>	—	59.7	—	ns	
Storage Time	t <sub>S</sub>	—	190.8	—	ns	
Fall Time	t <sub>F</sub>	—	108.6	—	ns	

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

# Typical Electrical Characteristics



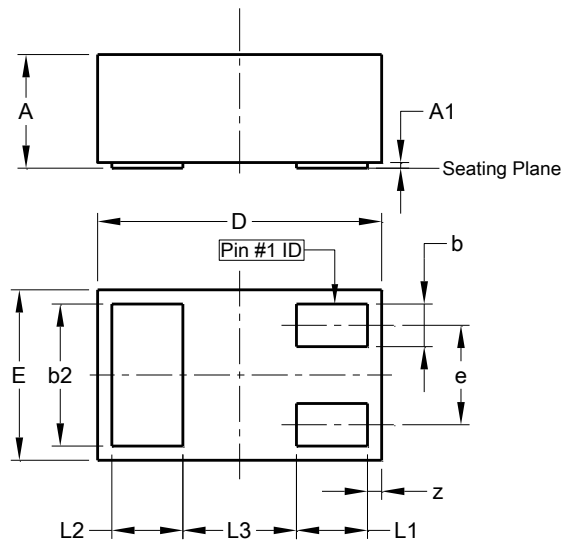
## Typical Electrical Characteristics (Cont.)



## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### X2-DFN1006-3

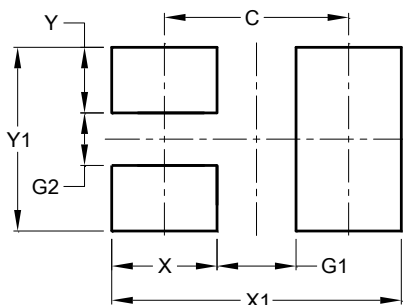


X2-DFN1006-3			
Dim	Min	Max	Typ
A	—	0.40	—
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.05	1.00
E	0.55	0.65	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### X2-DFN1006-3



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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